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DOCKF

GILLETTE 1012

	Application No.	Applicant(s)
Office Action Summary	11/183,463	CHISTYAKOV, ROMAN
	Examiner	Art Unit
	Rodney G. McDonald	1795
The MAILING DATE of this communication a Period for Reply	ppears on the cover sheet wi	th the correspondence address
<ul> <li>A SHORTENED STATUTORY PERIOD FOR REP WHICHEVER IS LONGER, FROM THE MAILING</li> <li>Extensions of time may be available under the provisions of 37 CFR <sup>-</sup> after SIX (6) MONTHS from the mailing date of this communication.</li> <li>If NO period for reply is specified above, the maximum statutory perio</li> <li>Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).</li> </ul>	DATE OF THIS COMMUNIC 1.136(a). In no event, however, may a re d will apply and will expire SIX (6) MON ute, cause the application to become AB	CATION. apply be timely filed THS from the mailing date of this communicatio ANDONED (35 U.S.C. § 133).
Status		
<ul> <li>1) Responsive to communication(s) filed on <u>14</u></li> <li>2a) This action is <b>FINAL</b>. 2b) Th</li> <li>3) Since this application is in condition for allow closed in accordance with the practice under</li> </ul>	is action is non-final. ance except for formal matte	•
Disposition of Claims		
<ul> <li>4) Claim(s) <u>31-75</u> is/are pending in the application 4a) Of the above claim(s) is/are withdres</li> <li>5) Claim(s) is/are allowed.</li> <li>6) Claim(s) <u>31-75</u> is/are rejected.</li> <li>7) Claim(s) is/are objected to.</li> <li>8) Claim(s) are subject to restriction and</li> </ul>	awn from consideration.	
Application Papers		
<ul> <li>9) The specification is objected to by the Examination 10) The drawing(s) filed on is/are: a) and a policant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the B</li> </ul>	ccepted or b) objected to t e drawing(s) be held in abeyan ection is required if the drawing(	ce. See 37 CFR 1.85(a). s) is objected to. See 37 CFR 1.121(
Priority under 35 U.S.C. § 119		
<ul> <li>12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority docume</li> <li>2. Certified copies of the priority docume</li> <li>3. Copies of the certified copies of the priority application from the International Bure</li> <li>* See the attached detailed Office action for a list</li> </ul>	nts have been received. nts have been received in A iority documents have been au (PCT Rule 17.2(a)).	oplication No received in this National Stage
Attachment(s) 1) X Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		ummary (PTO-413) )/Mail Date formal Patent Application

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#### **DETAILED ACTION**

#### Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set

forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this

application is eligible for continued examination under 37 CFR 1.114, and the fee set

forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action

has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on April

14, 2010 has been entered.

RM

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that

form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 31-46, 64-71 and 73-75 are rejected under 35 U.S.C. 102(e) as being

anticipated by Kouznetsov (WO 02/103078 A1).

Regarding claim 31, Kouznetsov teach a sputtering source comprising a cathode

assembly comprising a sputtering target that is positioned adjacent to an anode; and a

power supply that generates a voltage pulse between the anode and the cathode

assembly that creates a weakly ionized plasma and then a strongly ionized plasma from

the weakly ionized plasma without an occurrence of arcing between the anode and the

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cathode assembly, an amplitude a duration and a rise time of the voltage pulse being chosen to increase a density of ions in the strongly ionized plasma. (See Abstract; Page 9 lines 18-33; Page 11 lines 27-30; Page 12 lines 3-7; Page 13 lines 23-29; Page 15 lines 2-13; Page 21 lines 25-27; Page 22 lines 11-17; Figs. 8b; Fig. 10)

Regarding claim 32, Kouznetsov teach that the strongly ionized plasma at least partially converts neutral sputtered atoms into positive ions in order to enhance the sputtering process with ionized physical vapor deposition. (Page 18 lines 16-20)

Regarding claims 33, 34, Kouznetsov teach inherently based on the voltage pulse an increase in the density of ions which inherently generates sufficient thermal energy to cause a sputtering yield to be related to a temperature of the target.

Regarding claim 35, Kouznetsov teach the thermal energy generated in the sputtering target does not increase an average temperature of the sputtering target due to cooling. (See Fig. 12a)

Regarding claim 36, Kouznetsov teach a gas inlet to control the flow of the feed gas so that the feed gas diffuses the strongly ionized plasma. (Page 23 lines 10-11)

Regarding claim 37, Kouznetsov teach a gas inlet to control the flow of feed gas to allow additional power to be absorbed by the strongly ionized plasma, thereby generating additional thermal energy in the sputtering target. (Page 23 lines 10-11)

Regarding claim 38, Kouznetsov teach a magnet that is positioned to generate a magnetic field proximate to the weakly ionized plasma, the magnetic field substantially trapping electrons in the weakly-ionized plasma proximate to the sputtering target. (Page 11 lines 27-30)

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Regarding claim 39, Kouznetsov teach the voltage pulse generated between the anode and the cathode assembly excites atoms in the weakly ionized plasma and generates secondary electrons from the cathode assembly, the secondary electrons ionizing a portion of the excited atoms, thereby creating the strongly ionized plasma. (Page 15 lines 2-13)

Regarding claim 40, Kouznetsov teach the power supply generates a constant power. (Page 5 lines 23-25)

Regarding claim 41, Kouznetsov teach the power supply generates a constant voltage. (Page 5 lines 23-25)

Regarding claim 42, Kouznetsov teach a rise time. (See Figs. 9, 10)

Regarding claim 43, Kouznetsov teach a distance between the anode and the cathode for generating the plasma. (See Fig. 12a)

Regarding claim 44, Kouznetsov teach the rise time to be approximately within Applicant's range. (Page 23 lines 12-17)

Regarding claim 45, Kouznetsov teach the amplitude of the voltage pulse in the range of .4 to 4 kV. (Page 23 lines 13-14)

Regarding claim 46, Kouznetsov teach the pulse width of the voltage pulse in the range of approximately 0.1 microsecond to 100 seconds. (Page 23 lines 12-17)

Regarding claim 64, Kouznetsov teach a method for high deposition rate sputtering, the method comprising generating a voltage pulse between the anode and the cathode assembly comprising a sputtering target, the voltage pulse creating a weakly ionized plasma and then a strongly ionized plasma from the weakly ionized

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